

UPG10N60E

Preliminary

Insulated Gate Bipolar Transistor

600V, SMPS N-CHANNEL IGBT

DESCRIPTION

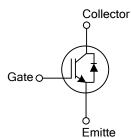
The UTC **UPG10N60E** is a N-channel IGBT. it uses UTC's advanced technology to provide customers with high input impedance, high switching speed and low conduction loss, etc.

The UTC **UPG10N60E** is suitable for high voltage switching, high frequency switch mode power supplies.

FEATURES

- * $V_{CE(SAT)} \le 1.95V$ @ I_C=20A, V_{GE}=15V
- * High switching speed
- * High input impedance
- * Low conduction loss

SYMBOL



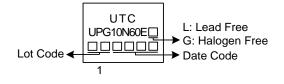
TO-220F1

ORDERING INFORMATION

| Ordering Number | | Deelvere | Pin Assignment | | | Deaking | |
|---|--------------|----------|----------------|---|---|---------|--|
| Lead Free | Halogen Free | Package | 1 | 2 | 3 | Packing | |
| UPG10N60EL-TF1-T UPG10N60EG-TF1-T | | TO-220F1 | G | С | Е | Tube | |
| Note: Pin Assignment: G: Gate C: Collector E: Emitter | | | | | | | |
| | | | | | | | |

| UPG10N60EG-TF1-T | |
|------------------|---|
| (1)Packing Type | (1) T: Tube |
| (2)Package Type | (2) TF1: TO-220F1 |
| (3)Green Package | (3) G: Halogen Free and Lead Free, L: Lead Free |
| | |

MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_c=25°C, unless otherwise specified)

| PARAMETER | | SYMBOL | RATINGS | UNIT |
|------------------------------------|-----------------------|------------------|------------|------|
| Collector-Emitter Voltage | | V _{CES} | 600 | V |
| Gate to Emitter Voltage Continuous | | V _{GES} | ±20 | V |
| | T _C =25°C | | 20 | А |
| Continuous Collector Current | T _C =100°C | l _C | 10 | А |
| Collector Current Pulsed (Note 2) | | I _{CM} | 30 | А |
| Orationary Frances Orange | T _C =25°C | | 10 | Α |
| Continuous Forward Current | T _C =100°C | I _F | 5 | А |
| Forward Current Pulsed | | I _{FM} | 80 | А |
| Peak Diode Recovery dv/dt (Note 3) | | dv/dt | 6.8 | V/ns |
| Power Dissipation | | P _D | 28 | W |
| Junction Temperature | | ΤJ | -55 ~ +150 | °C |
| Storage Temperature Range | | T _{STG} | -55 ~ +150 | °C |

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $I_F \le 10A$, di/dt $\le 200A/\mu s$, $V_{CC} \le BV_{CES}$, Starting $T_J=25^{\circ}C$

THERMAL DATA

| PARAMETER | SYMBOL | RATINGS | UNIT |
|------------------|-----------------|---------|------|
| Junction to Case | θ _{JC} | 4.46 | °C/W |

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN | TYP | MAX | UNIT |
|--------------------------------------|----------------------|--|----------|-----|-----|------|------|
| OFF CHARACTERISTICS | | | | | | | |
| Collector-Emitter Breakdown Voltage | BV _{CES} | I _C =250μA, V _{GE} =0V | | 600 | | | V |
| Collector-Emitter Leakage Current | I _{CES} | V _{CE} =600V, V _{GE} =0V | | | | 10 | μA |
| Gate to Emitter Leakage Current | I _{GES} | $V_{CE}=0V, V_{GE}=\pm 20V$ | | | | ±400 | nA |
| ON CHARACTERISTICS | | | | | | | |
| | V _{CE(SAT)} | I _C =10A, V _{GE} =15V | TJ=25°C | | 1.6 | 1.95 | V |
| Collector-Emitter Saturation Voltage | | | TJ=150°C | | 1.7 | | V |
| Gate to Emitter Threshold Voltage | V _{GE(TH)} | I _C =250µA, V _{CE} =V _{GE} | | 4.0 | | 6.5 | V |
| DYNAMIC CHARACTERISTICS | | | | | | | |
| Input Capacitance | CIES | V _{CE} =30V, V _{GE} =0V, f=1MHz | | | 418 | | рF |
| Output Capacitance | COES | | | | 53 | | рF |
| Reverse Transfer Capacitance | C _{RES} | | | | 8.9 | | pF |
| SWITCHING CHARACTERISTICS | | | | | | | |
| Total Gate Charge | Q_{G} | I _C =10A, V _{CE} =100V, V _{GE} =10V | | | 15 | | nC |
| Gate-Emitter Charge | Q_{GE} | | | | 4.5 | | nC |
| Gate-Collector Charge | Q_{GC} | | | | 6 | | nC |
| Current Turn-On Delay Time | t _{D(ON)} | | | | 64 | | ns |
| Current Rise Time | t _R | I_{C} =10A, V _{CE} =50V, V _{GE} =15V, R _G =10Ω | | | 46 | | ns |
| Current Turn-Off Delay Time | t _{D(OFF)} | | | | 56 | | ns |
| Current Fall Time | t _F | | | | 45 | | ns |
| DRAIN-SOURCE DIODE CHARACTER | ISTICS | | | | | | |
| Forward Voltage Drop | V _{FM} | I _F =4A | | | | 2.6 | V |
| Reverse Recovery Time | t _{rr} | I _F =4A, dl/dt=100A/µS, V _{CC} =400V | | | 66 | | ns |
| Reverse Recovery Charge | Qrr | | | | 140 | | nC |
| Nata: Dulas Test: Dulas width < 50.0 | | | | | | | |

Note: Pulse Test: Pulse width $\leq\!50\mu s.$



TEST CIRCUIT AND WAVEFORMS

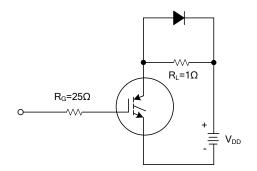


Fig 1. INDUCTIVE SWITCHING TEST CIRCUIT

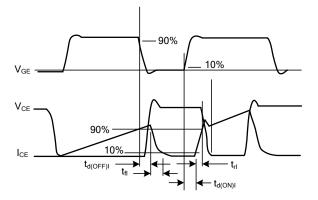


Fig 2. SWITCHING TEST WAVEFORMS

UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

